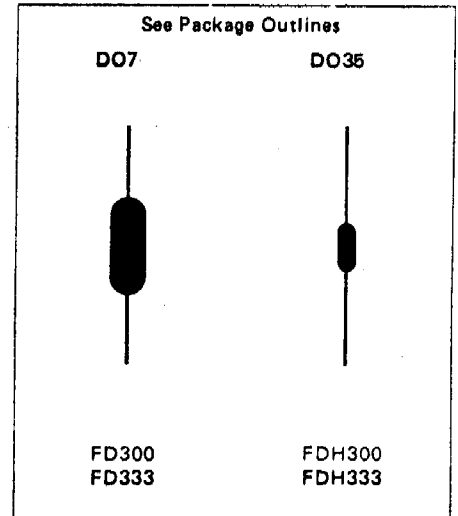


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FD300 • FD333 • FDH300 • FDH333

HIGH CONDUCTANCE LOW LEAKAGE
 DIFFUSED SILICON PLANAR DIODES



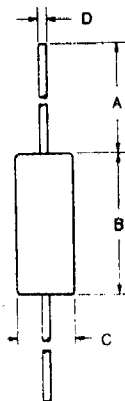
ABSOLUTE MAXIMUM RATINGS

Maximum Temperatures			
Storage Temperature		-65°C to +200°C	
Operating Temperature		175°C	
Maximum Power Dissipation (Notes 2 & 3)		FD300, FD333	FDH300, FDH333
Total Dissipation at 25°C Ambient Temperature		400 mW	500 mW
Linear Derating Factor		2.67 mW/°C	3.33 mW/°C
Maximum Voltages and Currents			
WIV	Working Inverse Voltage	125 V	125 V
I _O	Average Rectified Current	150 mA	200 mA
I _F	Forward Current Steady State	375 mA	500 mA
I _F	Recurrent Peak Forward Current	450 mA	600 mA
i _F (surge)	Peak Forward Surge Current		
	Pulse Width = 1.0 s	500 mA	1000 mA
	Pulse Width = 1.0 μs	4000 mA	4000 mA

ELECTRICAL CHARACTERISTICS (25°C Ambient Temperature unless otherwise noted)

SYMBOL	CHARACTERISTIC	FD300, FDH300		FD333, FDH333		UNITS	TEST CONDITIONS
		MIN.	MAX.	MIN.	MAX.		
V _F	Forward Voltage			0.9	1.15	V	I _F = 300 mA
				0.88	1.08	V	I _F = 250 mA
			1.0	0.87	1.05	V	I _F = 200 mA
				0.86	0.97	V	I _F = 150 mA
			0.92	0.83	0.94	V	I _F = 100 mA
			0.88	0.80	0.89	V	I _F = 50 mA
			0.8			V	I _F = 10 mA
			0.75			V	I _F = 5.0 mA
			0.68			V	I _F = 1.0 mA
I _R	Reverse Current		1.0		3.0	nA	V _R = -125 V
			3.0			μA	V _R = -125 V, T _A = 150°C
C	Capacitance		6.0		500	nA	V _R = -125 V, T _A = 100°C
BV	Breakdown Voltage	150		150		pF	V _R = 0
						V	I _R = 100 μA

DO35



DIM.	INCHES			MILLIMETERS		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	1.0			25.40		
B			.180			4.57
C			.075			1.91
D		.020			0.508	



Quality Semi-Conductors